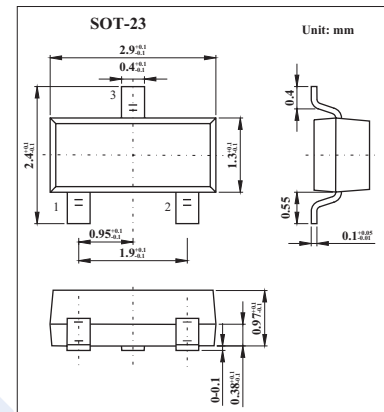
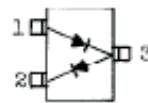


Silicon Epitaxial Planar Diode

1SS379

■ Features

- Low forward voltage : $V_F=1.0V$ (Typ.)
- Low reverse current: $I_R=0.1nA$ (Typ.)
- Small total capacitance: $C_T=3.0pF$ (Typ.)



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Maximum (peak) reverse voltage	V_{RM}	85	V
Reverse voltage	V_R	80	V
Average forward current *	I_o	100	mA
Maximum (peak) forward current *	I_{FM}	300	mA
Surge current (10 ms) *	I_{FSM}	2	A
Power dissipation	P	150	mW
Junction Temperature	T_j	125	$^\circ C$
Storage Temperature	T_{stg}	-55 + 125	$^\circ C$

* Unit Rating. Total Rating=Unit Rating X0.7

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Forward voltage	$V_{F(1)}$	$I_F = 100mA$		1.0	1.3	V
Reverse current	I_R	$V_R = 80V$		0.1	10	μA
Total capacitance	C_T	$V_R = 0, f = 1.0 MHz$		3.0	6.0	pF

■ Marking

Marking	P9